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Mode mixing performance evaluation and influence of elements on the fiber system behaviour

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Abstract: This study has clarified various micro electro mechanical system (MEMS) processes performance evaluation based on MEMSolver simulation software. The spin time against final resist thickness for the spin coating of a thin film of photo resist and the oxidation time versus oxide thickness for silicone dioxide growth for <100> silicon in wet oxide are clarified. The diffusion profile for Boron after predeposition and drive in of dopants in silicon and the thickness of silicon dioxide mask for Boron diffusion are demonstrated. The dopant distribution resulting from ion implantation and drive in and the percentage of dose

penetrating photo resist mask versus thickness of the mask are reported. The film stress versus the film thickness from wafer bow measurements, aluminum deposition rate against temperature using the electronic beam evaporator and the deposition rate of polysilicon versus silane partial pressure are reported. The etch rate of the thermal oxide against percentage concentration of KOH, the etch rate against the etchant temperature for silicon nitride in hot phosphoric acid, and the etch rate against the etchant temperature for the thermal oxide using buffered hydrofluoric acid (BOE) are outlined.

Keywords: diffusion; film deposition and wet etching; implantation; lithography; oxidation.

1 Introduction

There are many types of processes in MEMS such as lithography, oxidation, diffusion, implantation, film deposition and wet etching [1–9]. The lithography process includes the spin resist where the spin coating of a thin film of photo resist is studied [10–22]. The oxidation process includes the oxidation time in order to estimate the oxidation time to grow the silicon dioxide [23–36]. The diffusion process includes the traditional diffusion which the diffusion profile for the predeposition and drive-in in silicon [37–45]. The diffusion mask is clarified based on the silicon dioxide mask for high temperature diffusion [46–57]. The implementation process includes the traditional implantation which the ion implantation and drive in of main dopants in silicon [58–70]. The implant mask which the mask thickness for selective implantation of dopants are reported mathematically [71–85]. The film Deposition includes the film stress which the thin film stress to be estimated mathematically from wafer bow measurements [86–95]. The evaporation process which the deposition rate of metals using E-beam planetary evaporator is evaluated by using the mathematical relations [96–107]. The wet etching process includes KOH etching, membrane etch, phosphoric acid and buffered HF

***Corresponding authors: Md. Amzad Hossain**, Institute of Theoretical Electrical Engineering, Faculty of Electrical Engineering and Information Technology, Ruhr University Bochum, 44801 Bochum, Germany; and Department of Electrical and Electronic Engineering, Jashore University of Science and Technology, 7408 Jashore, Bangladesh, E-mail: mahossain.eee@gmail.com; and **Ahmed Nabih Zaki Rashed**, Electronics and Electrical Communications Engineering Department, Faculty of Electronic Engineering, Menoufia University, 32951 Menouf, Egypt; and Department of VLSI Microelectronics, Institute of Electronics and Communication Engineering, Saveetha School of Engineering, SIMATS, 602105 Chennai, Tamilnadu, India, E-mail: ahmed_733@yahoo.com. <https://orcid.org/0000-0002-5338-1623>

Shanmugapriya Ganesan, Department of ECE, Agnel Institute of Technology and Design, Goa, India, E-mail: spriyagsn@yahoo.com

Suneela Bhoompally, Department of ECE, Malla Reddy Engineering College, 500043 Telagana, India, E-mail: sunilareddyk@gmail.com

Shaik Hasane Ahammad, Department of ECE, Koneru Lakshmaiah Education Foundation, 522302 Vaddeswaram, Andhra Pradesh, India, E-mail: ahammadklu@gmail.com

Kasi Uday Kiran, Department of ECE, Koneru Lakshmaiah Education Foundation, 522502 Guntur, India, E-mail: uk_ace@kluniversity.in

Twana Mohammed Kak Anwer, Department of Physics, College of Education, Salahaddin University-Erbil, 44002 Erbil, Kurdistan Region, Iraq, E-mail: twana.anwar1@su.edu.krd

Walid Fahim Zidan, Electronics and Electrical Communications Engineering Department, Faculty of Electronic Engineering, Menoufia University, 32951 Menouf, Egypt, E-mail: Walid.Fahim.Zidan9090@gmail.com

[108–120]. The phosphoric acid process which discuss the etch rate of silicon nitride and silicon dioxide in phosphoric acid. The buffered HF which discuss the etch rate of thermal oxide in buffered hydrofluoric acid (BOE) [121–145].

2 Models performance parameters and results discussions

Figure 1 clarifies the spin time against final resist thickness for the spin coating of a thin film of photoresist. The spin time decreases linearly with the final resist thickness varies from 0.1 to 40 μm . Where the initial height of resist is 400 μm , the desired final height of resist is 2 μm , rotational speed of chuck is 20,000 rpm, and kinematic viscosity of resist is 10,000 cSt. The spin coating of a thin film of photoresist is designed through the time of rotation of chuck is 7.122 min.

Figure 2 illustrates the oxidation time versus oxide thickness for silicon dioxide growth for <100> silicon in wet oxide. Where the oxide thickness is 0.5 μm , the oxidation Temperature is 1010 $^{\circ}\text{C}$ and atmosphere is Wet O_2 . The oxidation time increases linearly with the oxide thickness varies from 0.01 μm to 10 μm . In order to calculate oxidation time to grow silicon dioxide, the desired oxidation time in Wet oxide O_2 is 79.80 min.

Figure 3 shows the diffusion profile for Boron after predeposition and drive in of dopants in silicon. The Boron concentration decreases exponentially with the depth in silicone varies from 0.001 to 0.17 μm in the predeposition

case. The Boron concentration decreases exponentially with the depth in silicone varies from 0.001 to 1.6 μm in the drive in case. The Epi/Substrate wafer type is N-Type, the Epi/Substrate resistivity [ohm-cm] is 1, the dopant type is Boron, the temperature is 940 $^{\circ}\text{C}$, the time is 20 min, the temperature is 1100 $^{\circ}\text{C}$, the time is 45 min. The diffusion profile for pre-deposition and drive-in of dopants in silicon is designed. The surface concentration is $7.866\text{E}+018$ atoms/ cm^3 , Final junction depth is 1.539 μm and Sheet resistance is 216.44 Ω/sq .

Figure 4 illustrates the thickness of silicon dioxide mask for Boron diffusion. The silicon dioxide mask thickness increases linearly with the diffusion time varies from 10 min to 1000 min. Where the diffusion temperature is 1090 $^{\circ}\text{C}$, the diffusion time is 87 min and the dopant type is Boron. The silicon dioxide mask for high temperature diffusion is designed. So the thickness of the Silicon dioxide mask is 0.1551 μm .

Figure 5 indicates the dopant distribution resulting from ion implantation and drive in. The Boron concentration increases exponentially with the depth in silicon varies from 0.001 μm to 0.3 μm in the case of implant. But the Boron concentration increases exponentially with the depth in silicon varies from 0.31 μm to 1.4 μm in the case of drive in. Where the Epi/Substrate wafer type is N-Type, the Epi/Substrate resistivity is 1 $\Omega\text{-cm}$, the dopant Type is Boron, the implant energy is 80 keV, the Implant dose is $230,000,000,000,000/\text{cm}^2$, the temperature is 1070 $^{\circ}\text{C}$, the time is 45 min. The ion implantation and drive-in of dopants in silicon is designed to estimate the peak concentration is $6.505\text{E}+018$ atoms/ cm^3 , junction depth after

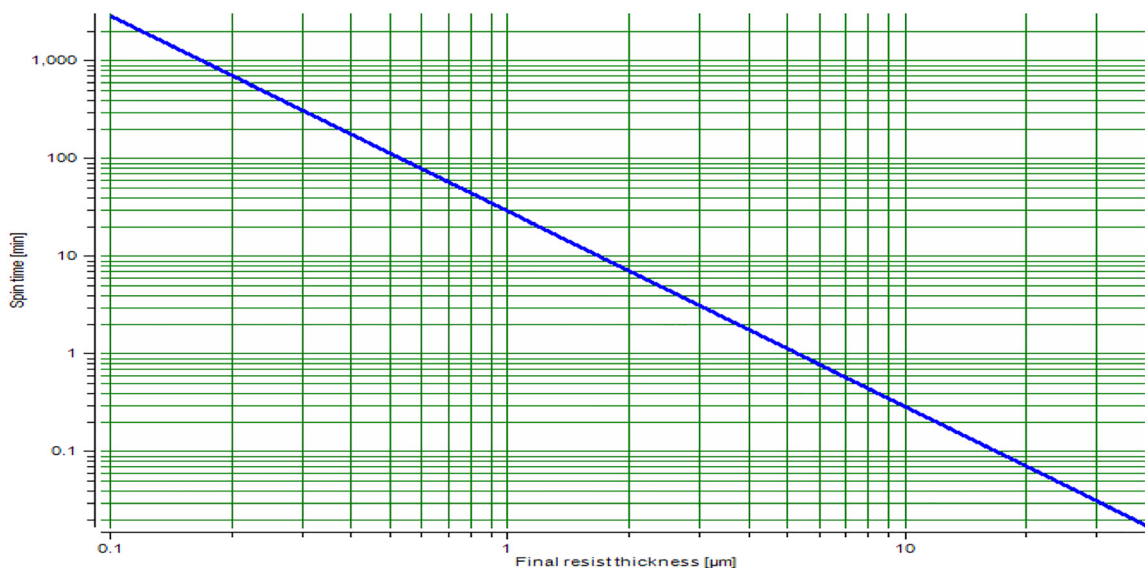


Figure 1: Spin time against final resist thickness.

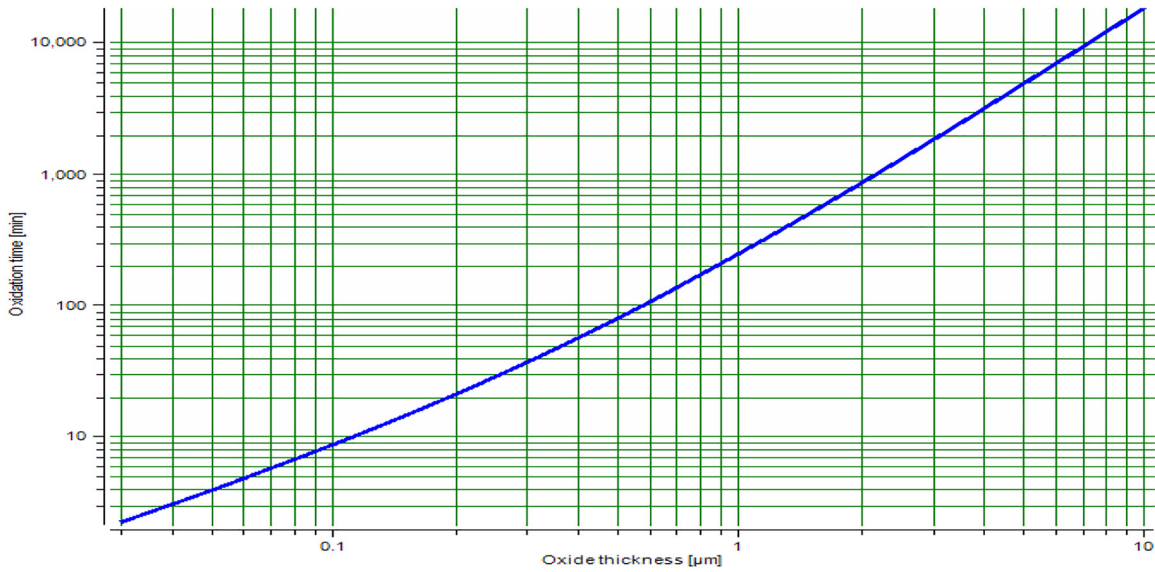


Figure 2: Oxidation time versus oxide thickness for silicone dioxide growth for <100> silicon in wet oxide.

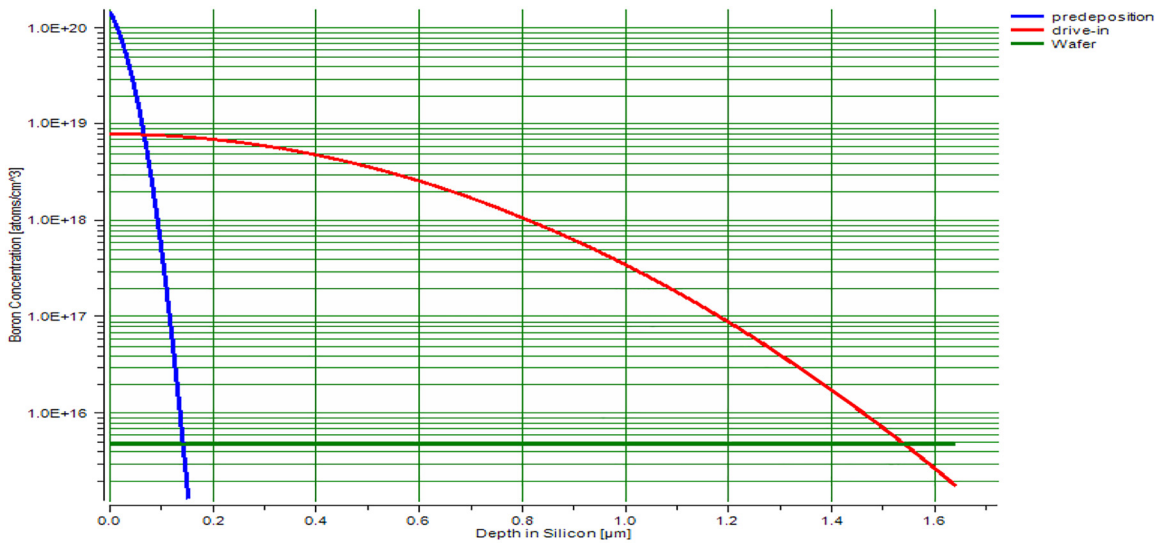


Figure 3: Boron concentration versus depth in silicon in predeposition, drive in cases.

drive-in is 1.412 μm and the sheet resistance after drive-in is 357.85 Ω/sq .

Figure 6 clarifies the percentage of dose penetrating photo resist mask versus thickness of the mask. The mask thickness decreases exponentially with the percentage of dose penetrating photo resist mask varies from 1 to 50%. Where the implant energy is 95 keV, the percentage of dose penetrating mask is 10% and the dopant type is Boron. The mask thickness for selective implantation of dopants is designed to estimate the minimum silicon dioxide mask thickness should be 0.389 μm and the minimum photo resist mask thickness should be 0.7391 μm .

Figure 7 illustrates the film stress versus the film thickness from wafer bow measurements. The film stress decreases linearly with the film thickness varies from 0.01 to 20 μm . Where the bow before deposition is 0.2 μm , the bow after deposition is 6 μm , the thickness of film is 0.2 μm , the thickness of substrate is 400 μm , the diameter of wafer is 100 mm, Young's modulus of substrate is 180 GPa and Poisson's ratio is 0.3. The thin film stress calculated from wafer bow measurements which gives the stress in the film is 159.086 MPa.

Figure 8 shows aluminum deposition rate against temperature using Electronic beam evaporator. Aluminum

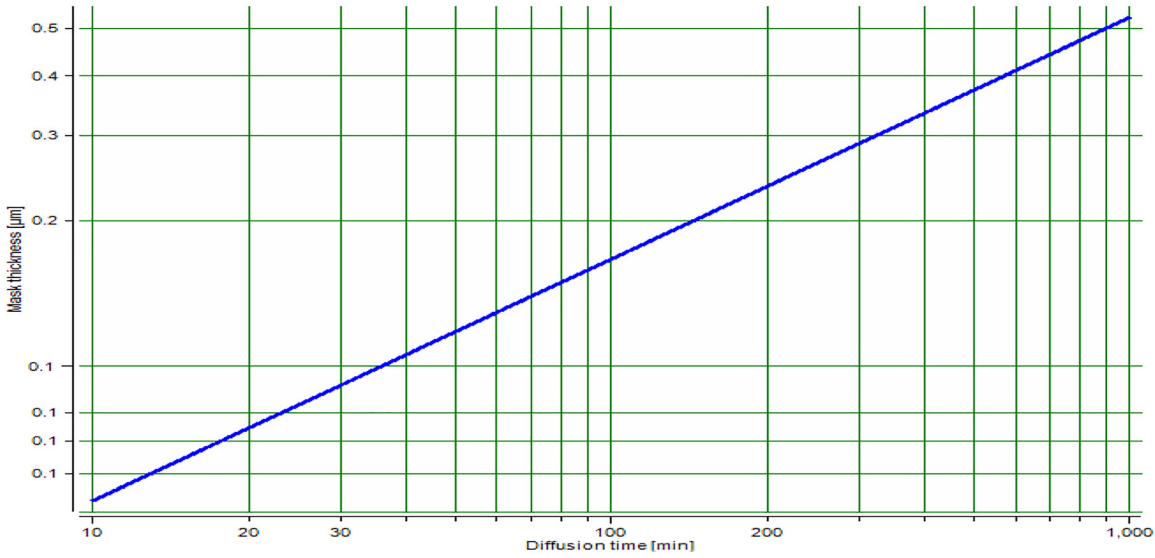


Figure 4: Mask thickness versus the diffusion time for Boron diffusion.

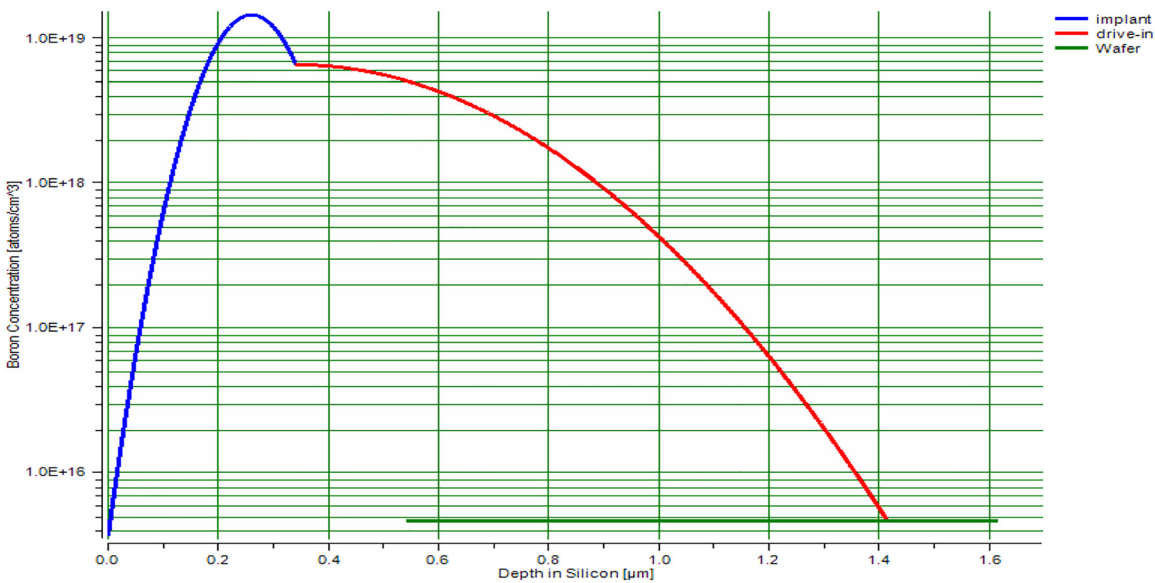


Figure 5: Boron concentration versus the depth in silicon from ion implantation and drive in.

deposition rate increases exponentially with the temperature varies from 900 to 1500 °C. Where the temperature of metal charge is 1150 °C, the radius of the planetary holder is 40 cm, the diameter of the crucible is 5 cm and evaporated metal is aluminum. The deposition rate of metals using E-beam planetary evaporator in order to estimate the deposition rate of Aluminum is 57.761 Å/min.

Figure 9 demonstrates the deposition rate of polysilicon versus silane partial pressure. The deposition rate increases exponentially with the silane partial pressure varies from 1 to 750 mTorr. Where the deposition temperature is 959 °C,

the percentage of silane concentration is 30% and the total pressure is 300 mTorr. The deposition rate of polysilicon using silane in a low pressure reactor is designed to give the polysilicon deposition rate is 57.9 Å/min.

Figure 10 illustrates the etch rate of the thermal oxide against percentage concentration of KOH. The etch rate increases linearly with the etchant concentration percentage varies from 10 to 30%, but The etch rate slightly changes as a flat step with the etchant concentration percentage varies from 31 to 35% and the etch rate decreases linearly with the etchant concentration

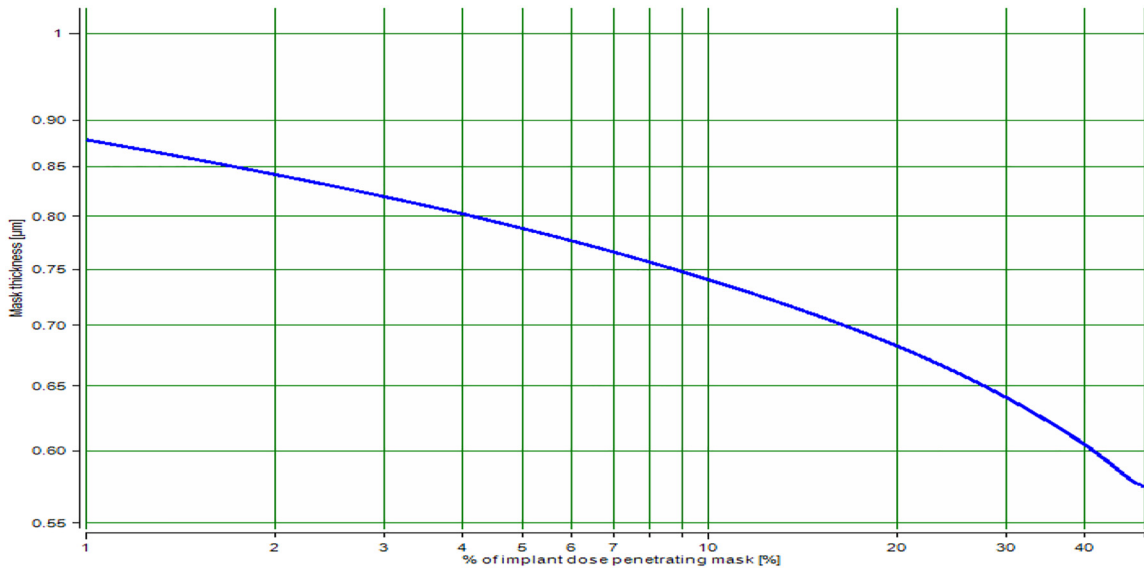


Figure 6: Percentage of dose penetrating photo resist mask versus thickness of the mask.

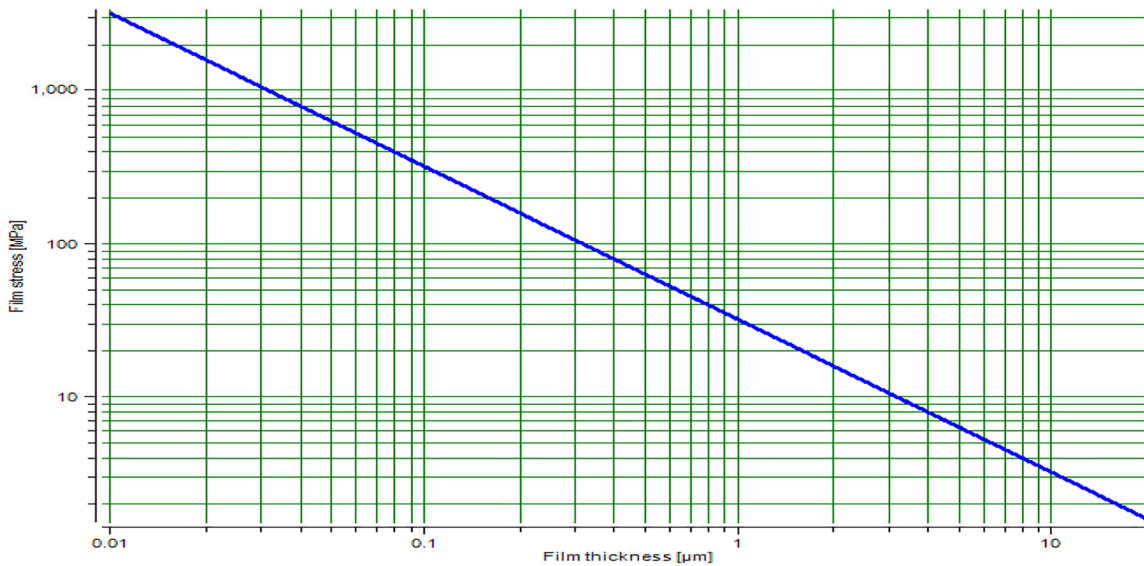


Figure 7: Film stress versus the film thickness from wafer bow measurements.

percentage varies from 36 to 60%. Where the etchant temperature is 30 °C, the etchant concentration is 45 wt% and the etchant is KOH/water. The etch rate of silicon and silicon dioxide in KOH is estimated to clarify the etch rate of <100> silicon in KOH/water etchant is 2.224 µm/h, Etch rate of <110> silicon in KOH/water etchant is 3.331 µm/h and Etch rate of thermal oxide in KOH/water etchant is 3.644 nm/h.

Figure 11 clarifies the mask opening versus the membrane thickness and the size of the mask opening for membrane etch using KOH is simulated. The mask opening

decreases linearly with the membrane thickness varies from 2 to 25 µm. Where the thickness of wafer is 400 µm, the thickness of membrane is 15 µm and the size of membrane is 1000 µm. To determine size of mask opening for membrane etch using KOH to give the size of the mask opening is 1545.3 µm.

Figure 12 demonstrates the etch rate against the etchant temperature for silicon nitride in hot phosphoric acid. The etch rate increases with the etchant temperature increases from 145 to 168 °C. Where the etchant temperature is 160 °C, the etchant concentration is 89 wt% and the

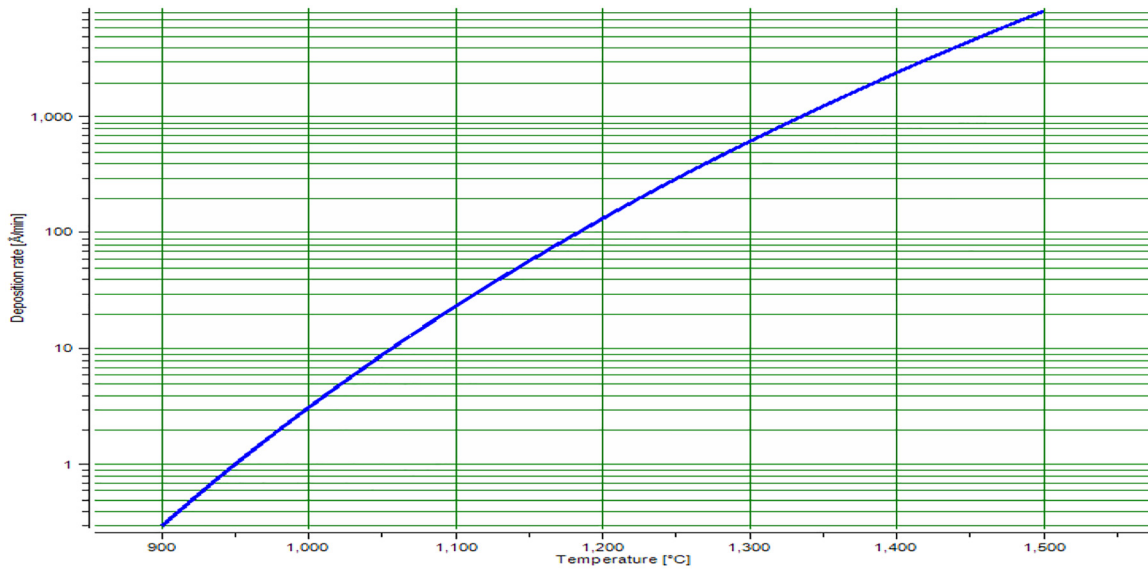


Figure 8: Aluminum deposition rate against temperature using electronic beam evaporator.

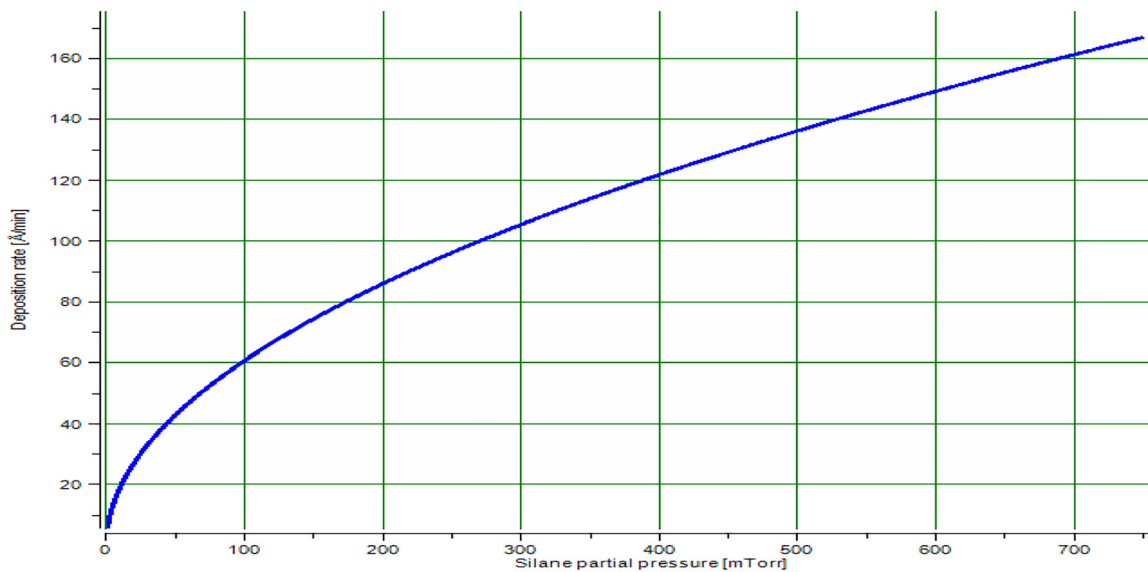


Figure 9: Deposition rate of polysilicon versus silane partial pressure.

film type is the silicon nitride. The etch rate of silicon nitride and silicon dioxide in phosphoric acid is estimated in order to clarify the etch rate at the given temperature is 49.34 Å/min and maximum etch rate at the given concentration is 74.05 Å/min.

Figure 13 shows the etch rate against the etchant temperature for the thermal oxide using BOE. The etch rate increases with the etchant temperature increases from 20 to 40 °C. The etchant temperature is 32 °C, the etchant concentration is 2.4 wt% and the film type is the thermal oxide. The etch rate of thermal oxide in buffered hydrofluoric acid

(BOE) is estimated in order to calculate the etch rate of thermal oxide in buffered HF is 600 Å/min.

3 Conclusions

Various MEMS processes performance evaluation based on MEMSolver simulation software have been simulated. The spin coating of a thin film of photo resist is designed through the time of rotation of chuck is 7.122 min. In order to calculate oxidation time to grow silicon dioxide, the

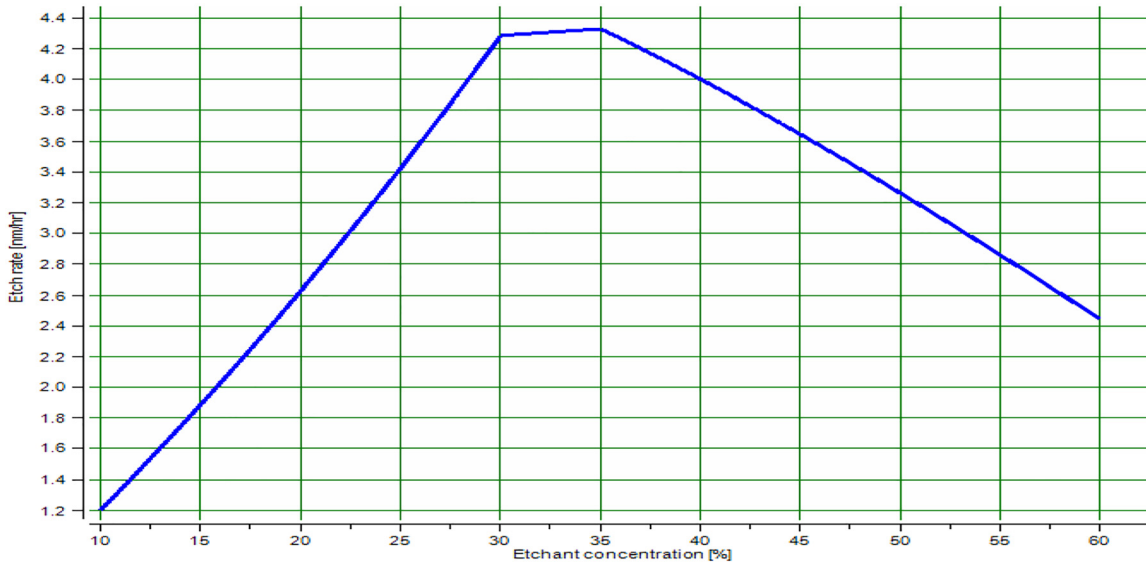


Figure 10: Etch rate against the etchant concentration percentage.

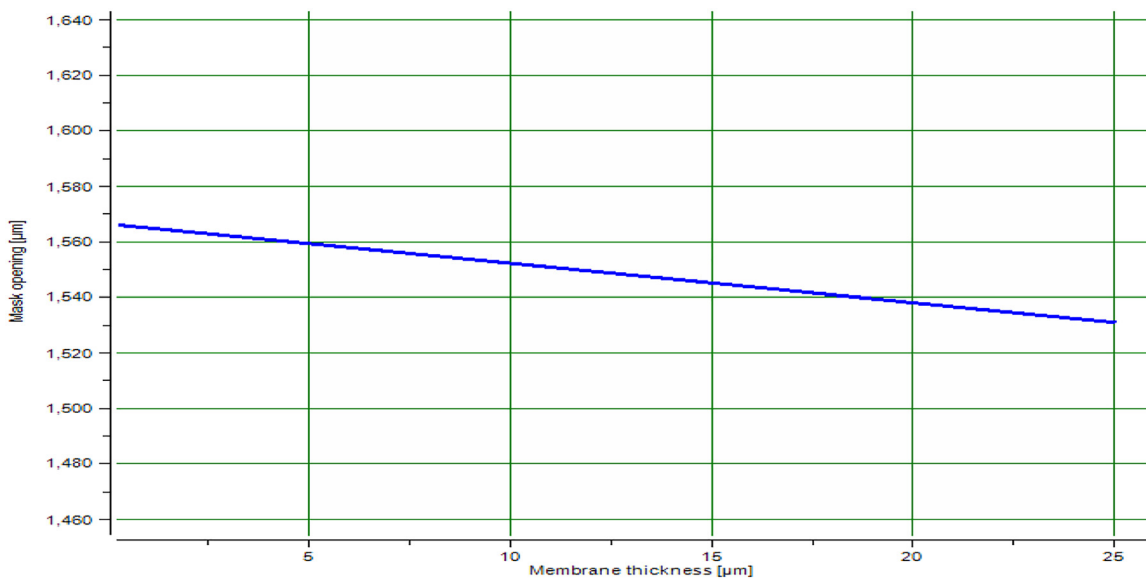


Figure 11: The size of the mask opening for membrane etch using KOH.

desired oxidation time in Wet oxide O_2 is 79.80 min. The diffusion profile for pre-deposition and drive-in of dopants in silicon is designed. The surface concentration is $7.866E+018$ atoms/cm³, Final junction depth is 1.539 μm and Sheet resistance is 216.44 Ω/sq. The silicon dioxide mask for high temperature diffusion is designed. So the thickness of the Silicon dioxide mask is 0.1551 μm. The ion implantation and drive-in of dopants in silicon is designed to estimate the peak concentration is $6.505E+018$ atoms/cm³, junction depth after drive-in is 1.412 μm and the sheet resistance after drive-in is 357.85 Ω/sq. The mask thickness for

selective implantation of dopants is designed to estimate the minimum silicon dioxide mask thickness should be 0.389 μm and the minimum photo resist mask thickness should be 0.7391 μm.

The thin film stress calculated from wafer bow measurements which gives the stress in the film is 159.086 MPa. The deposition rate of metals using E-beam planetary evaporator in order to estimate the deposition rate of Aluminum is 57.761 Å/min. The etch rate of silicon and silicon dioxide in KOH is estimated to clarify the etch rate of <100> silicon in KOH/water etchant is 2.224 μm/h, Etch rate of <110>

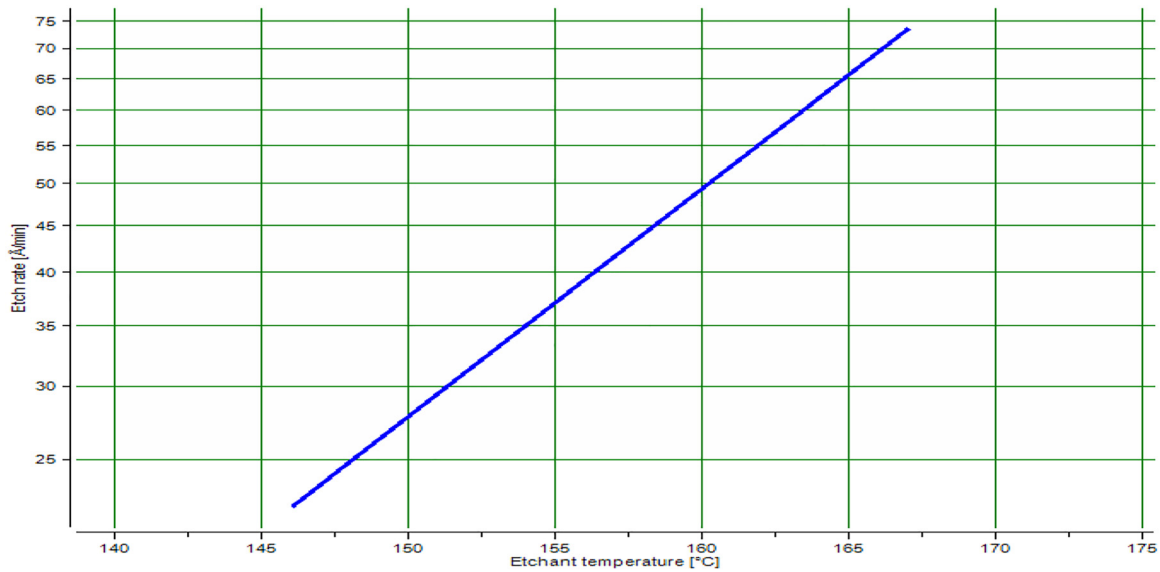


Figure 12: Etch rate against the etchant temperature for silicon nitride in hot phosphoric acid.

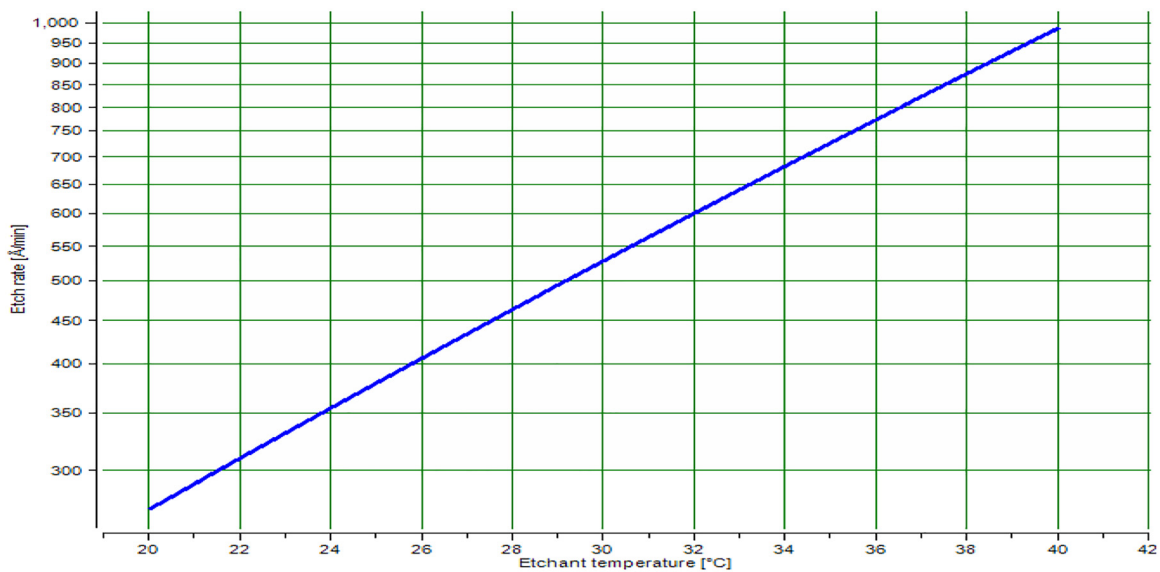


Figure 13: Etch rate against the etchant temperature for the thermal oxide using BOE.

silicon in KOH/water etchant is $3.331 \mu\text{m/h}$ and Etch rate of thermal oxide in KOH/water etchant is 3.644 nm/h . To determine size of mask opening for membrane etch using KOH to give the size of the mask opening is $1545.3 \mu\text{m}$. The etch rate of silicon nitride and silicon dioxide in phosphoric acid is estimated in order to clarify the etch rate at the given temperature is 49.34 \AA/min and maximum etch rate at the given concentration is 74.05 \AA/min . The etch rate of thermal oxide in buffered hydrofluoric acid (BOE) is estimated in

order to calculate the etch rate of thermal oxide in buffered HF is 600 \AA/min .

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